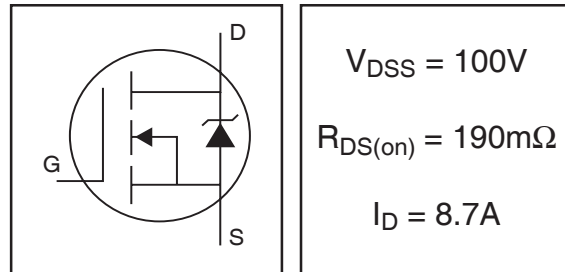


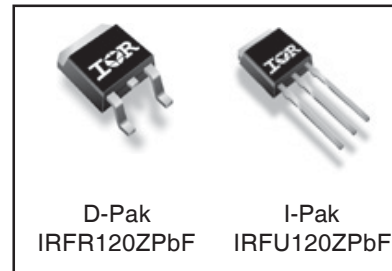
**Features**

- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free



**Description**

This HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in a wide variety of applications.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	8.7	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	6.1	
$I_{DM}$	Pulsed Drain Current ①	35	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	35	W
	Linear Derating Factor	0.23	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$ (Thermally limited)	Single Pulse Avalanche Energy ②	18	mJ
$E_{AS}$ (Tested)	Single Pulse Avalanche Energy Tested Value ③	20	
$I_{AR}$	Avalanche Current ④	See Fig.12a, 12b, 15, 16	A
$E_{AR}$	Repetitive Avalanche Energy ⑤		mJ
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

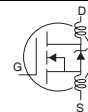
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	4.28	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount) ⑥	—	40	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

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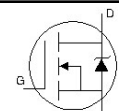
## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.084	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	150	190	m $\Omega$	$V_{GS} = 10V, I_D = 5.2A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
gfs	Forward Transconductance	16	—	—	S	$V_{DS} = 25V, I_D = 5.2A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 100V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$
$Q_g$	Total Gate Charge	—	6.9	10	nC	$I_D = 5.2A$
$Q_{gs}$	Gate-to-Source Charge	—	1.6	—		$V_{DS} = 80V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	3.1	—		$V_{GS} = 10V$ ③
$t_{d(on)}$	Turn-On Delay Time	—	8.3	—	ns	$V_{DD} = 50V$
$t_r$	Rise Time	—	26	—		$I_D = 5.2A$
$t_{d(off)}$	Turn-Off Delay Time	—	27	—		$R_G = 53\ \Omega$
$t_f$	Fall Time	—	23	—		$V_{GS} = 10V$ ③
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	310	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	41	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	24	—		$f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	150	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	26	—		$V_{GS} = 0V, V_{DS} = 80V, f = 1.0\text{MHz}$
$C_{oss\ eff.}$	Effective Output Capacitance	—	57	—		$V_{GS} = 0V, V_{DS} = 0V\ \text{to}\ 80V$ ④



## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	8.7	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	35		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 5.2A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	24	36	ns	$T_J = 25^\circ\text{C}, I_F = 5.2A, V_{DD} = 50V$
$Q_{rr}$	Reverse Recovery Charge	—	23	35	nC	$di/dt = 100A/\mu s$ ③
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				



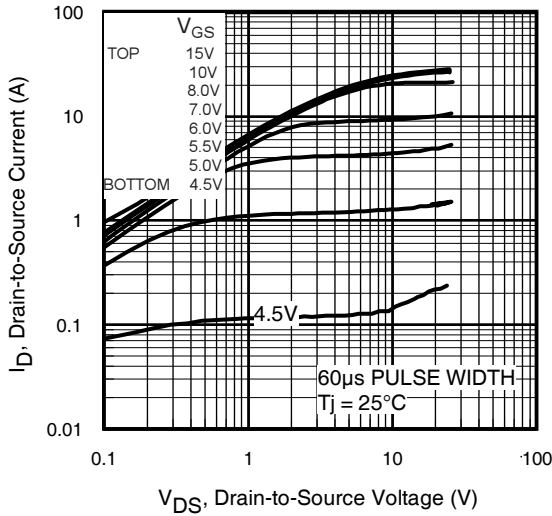


Fig 1. Typical Output Characteristics

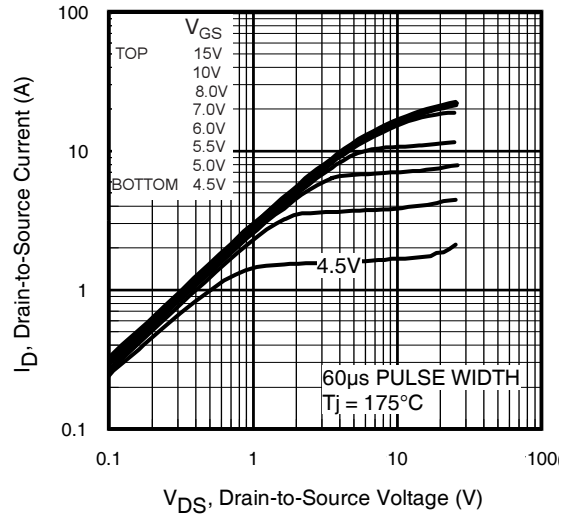


Fig 2. Typical Output Characteristics

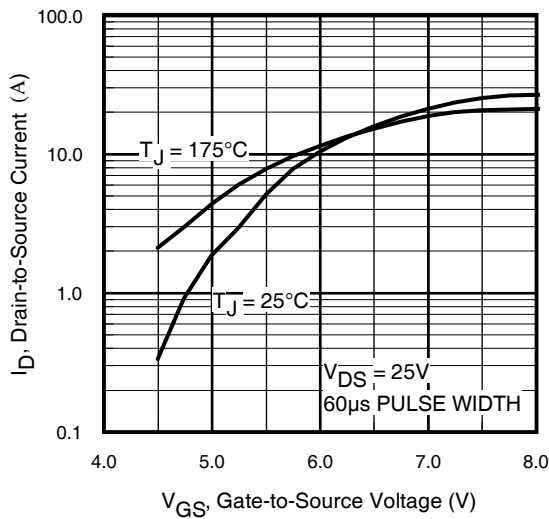


Fig 3. Typical Transfer Characteristics

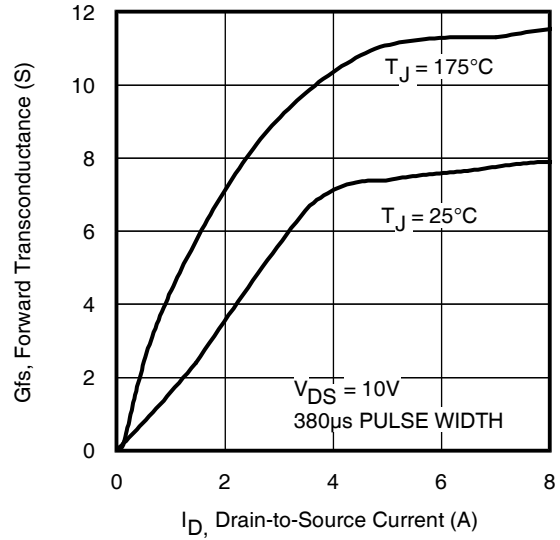
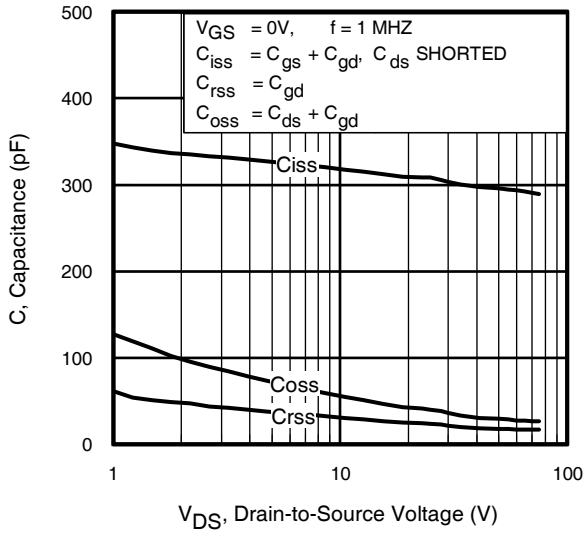
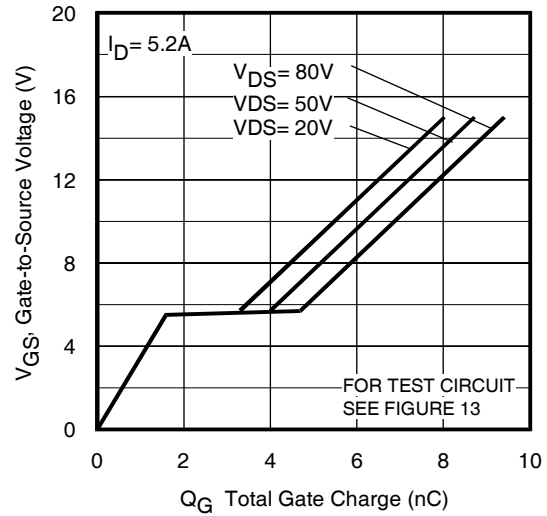


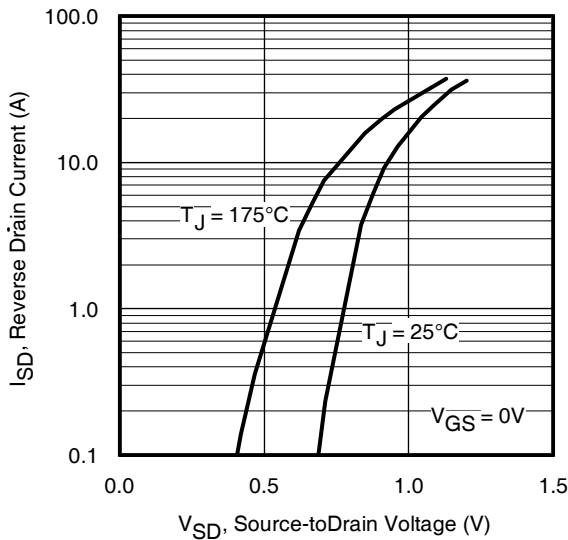
Fig 4. Typical Forward Transconductance Vs. Drain Current



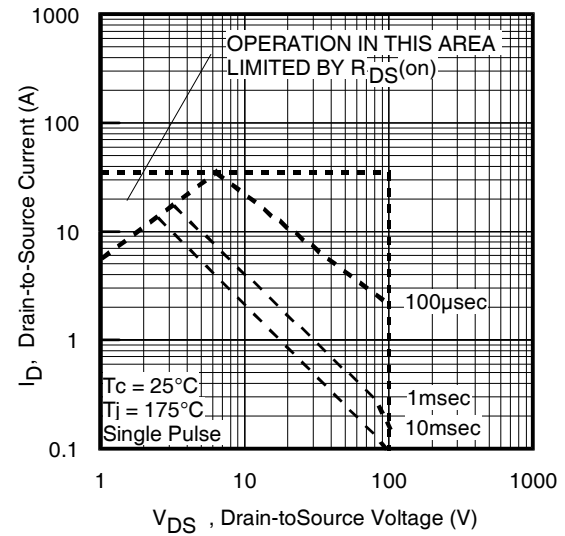
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



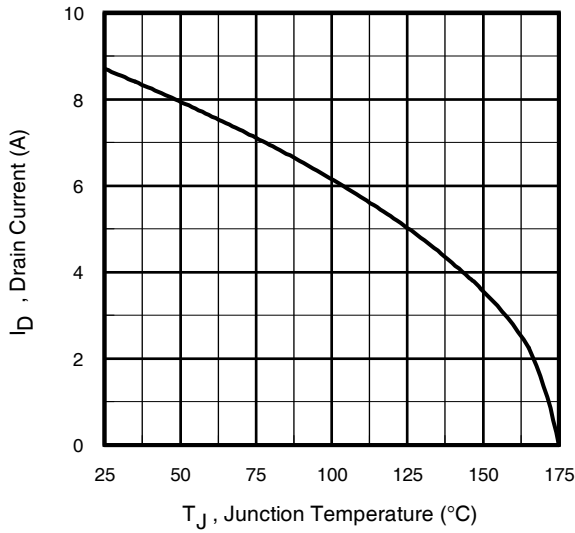
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



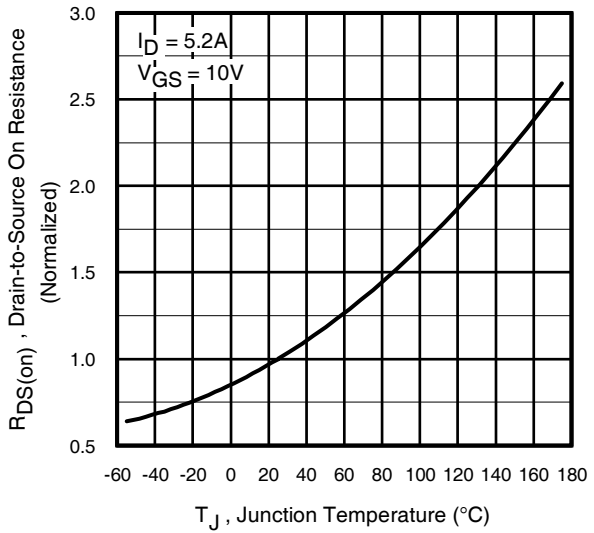
**Fig 7.** Typical Source-Drain Diode Forward Voltage



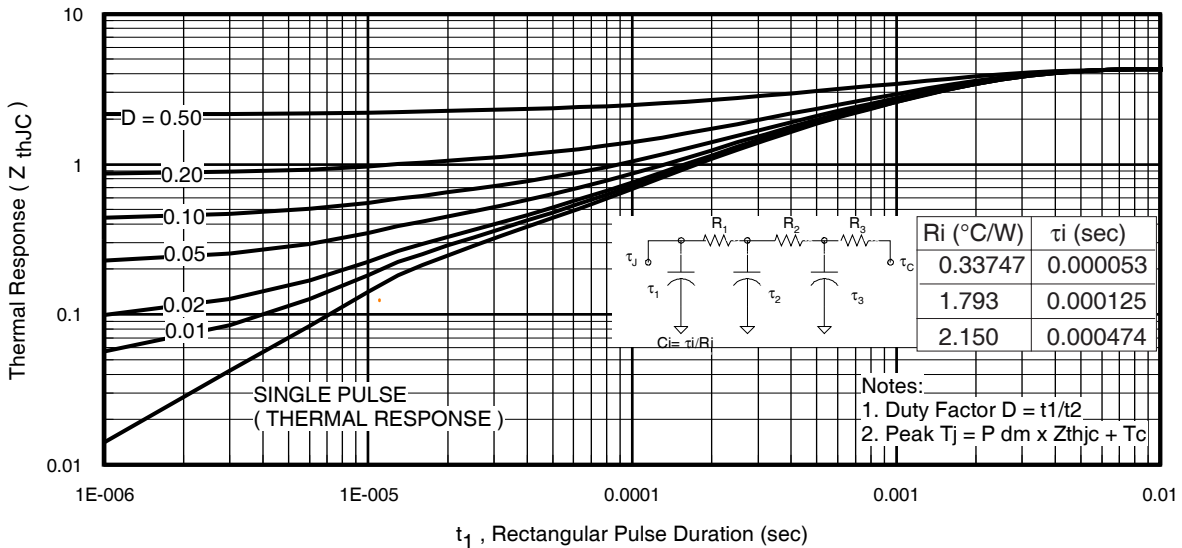
**Fig 8.** Maximum Safe Operating Area



**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10.** Normalized On-Resistance Vs. Temperature



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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**Fig 12a.** Unclamped Inductive Test Circuit



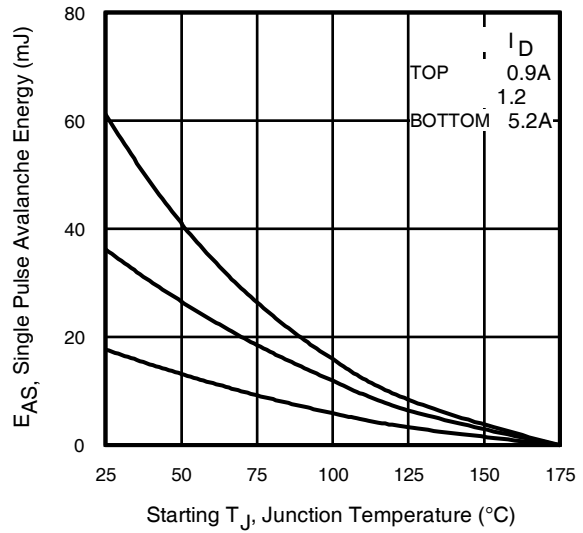
**Fig 12b.** Unclamped Inductive Waveforms



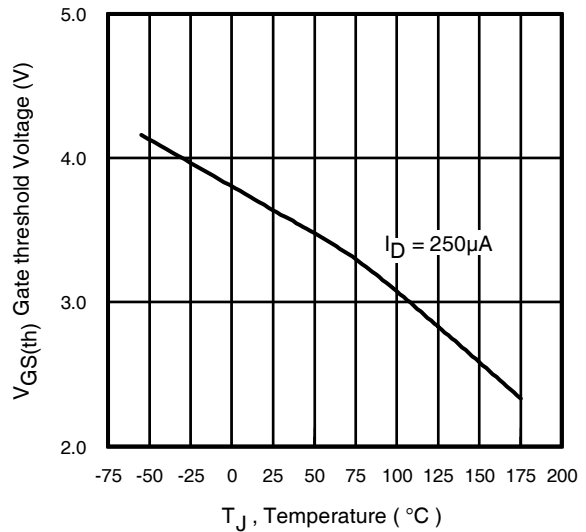
**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 14.** Threshold Voltage Vs. Temperature

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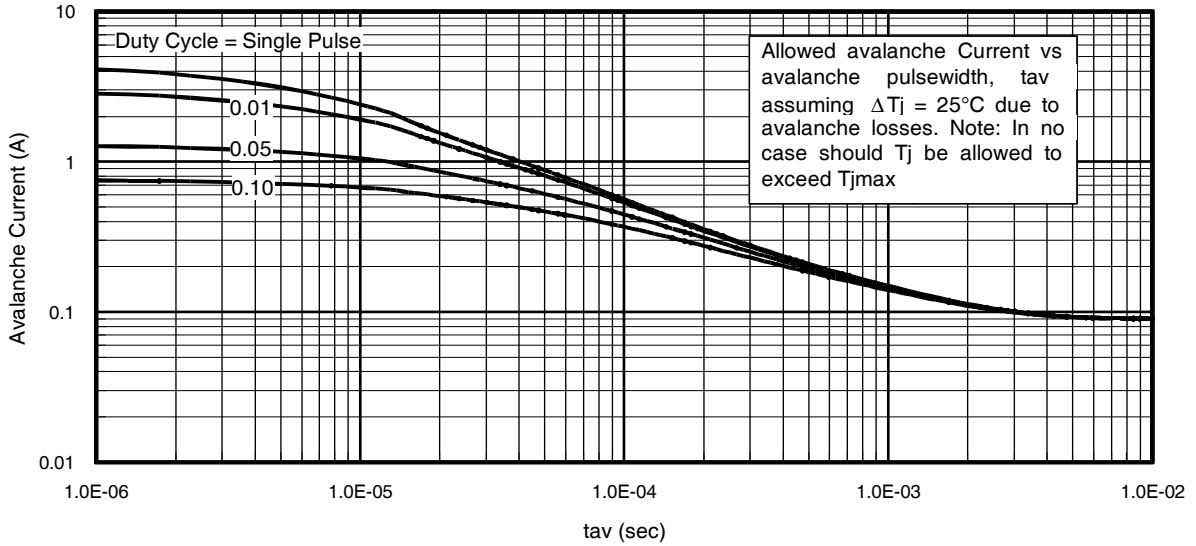


Fig 15. Typical Avalanche Current Vs.Pulsewidth

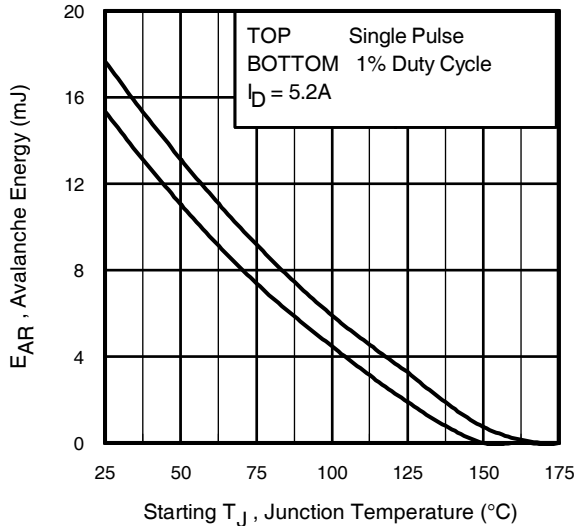


Fig 16. Maximum Avalanche Energy Vs. Temperature

**Notes on Repetitive Avalanche Curves , Figures 15, 16: (For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption: Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5.  $BV$  = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$



**Fig 17. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**



**Fig 18a. Switching Time Test Circuit**

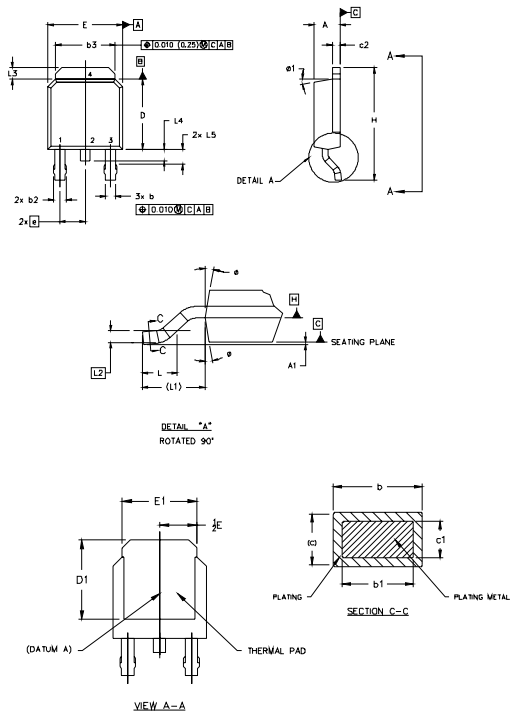


**Fig 18b. Switching Time Waveforms**



## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
- 3.0 LEAD DIMENSION UNCONTROLLED IN L5
- 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.254] FROM THE LEAD TIP.
- 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.15		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 REF.		.108 REF.		
L2	0.051 BSC		.020 BSC		
L3	0.69	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	
a	0"	10"	0"	10"	
a1	0"	15"	0"	15"	

**LEAD ASSIGNMENTS**

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

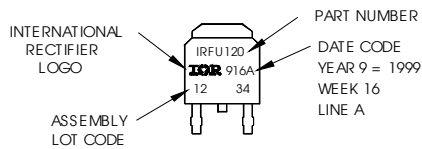
**IGBTs\_CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

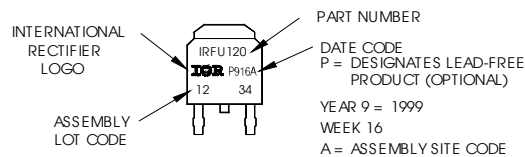
## D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 1999  
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position  
indicates "Lead-Free"



OR



### Notes:

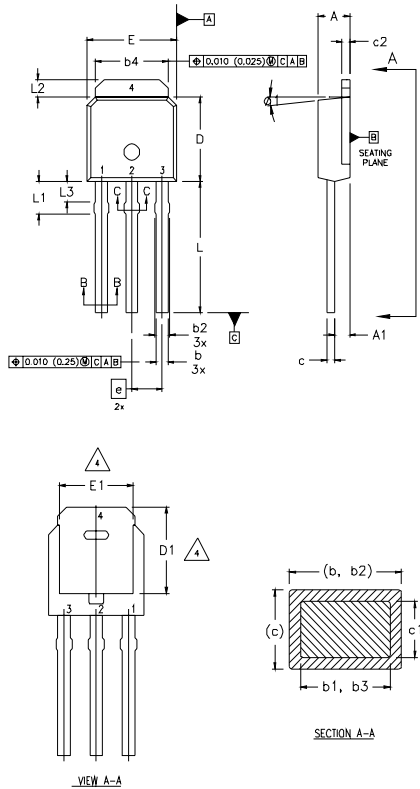
1. For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
2. For the most current drawing please refer to IR website at <http://www.irf.com/package/>

[www.irf.com](http://www.irf.com)

# IRFR/U120ZPbF

International  
**IR** Rectifier

## I-Pak (TO-251AA) Package Outline Dimensions are shown in millimeters (inches)



### NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

### LEAD ASSIGNMENTS

#### HEXFET

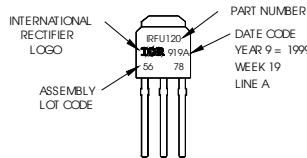
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	ø	15°	ø	15°	

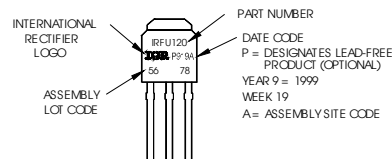
## I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120  
WITH ASSEMBLY  
LOT CODE 5678  
ASSEMBLED ON WW19, 1999  
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line  
position indicates "Lead-Free"



OR

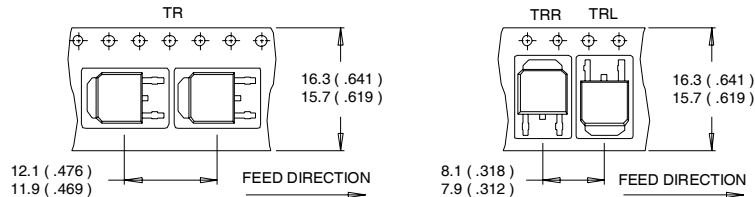


### Notes:

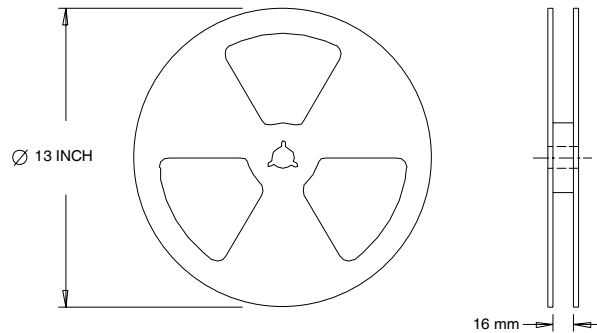
1. For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
2. For the most current drawing please refer to IR website at <http://www.irf.com/package/>

## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION: MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. OUTLINE CONFORMS TO EIA-481.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ C$ ,  $L = 1.29mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 5.2A$ ,  $V_{GS} = 10V$ . Part not recommended for use above this value.
- ③ Pulse width  $\leq 1.0ms$ ; duty cycle  $\leq 2\%$ .
- ④  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑤ Limited by  $T_{Jmax}$ , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑥ This value determined from sample failure population. 100% tested to this value in production.
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Industrial market.  
 Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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 TAC Fax: (310) 252-7903

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单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)